

Helios INLINE-tn

Coating Measurement of Solar Cells
Thickness and Refractive Index of Silicon Nitride



Helios INLINE-tn

For wafer based solar cells the anti-reflective coating, surface passivation and diffusion barrier play an important role to achieve high solar cell efficiency and long term stability. Because of its excellent characteristics Silicon Nitride coating (a-SiNx:H) is widely used for this purpose.

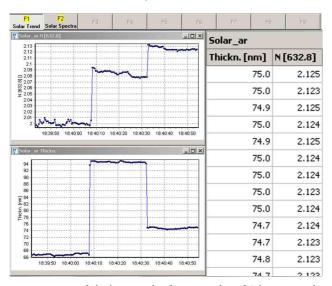
Process parameters such as the gas pressure and temperature of the cell during deposition have a strong influence on the layer thickness and the optical constants n&k of Silicon Nitride. Therefore, it is essential to gain detailed knowledge of the layer thickness and the optical constants n&k during the process. Conventional measurement technology can only measure Silicon Nitride layer properties offline and on polished wafers.

Inline Measurement of Silicon Nitride

NXT offers unique equipment to measure layer thickness as well as refractive index of the Silicon Nitride layer. The Helios INLINE-tn system is designed for inline use and can be retrofitted in existing production lines!

Improve the quality and efficiency of your cells, via finding and reducing the causes of process instabilities and inhomogenities, such as coater inhomogeneities, coater drift and impact of sawing and texturing inhomogeneities.

Measurement Example



Measurement of thickness and refractive index of Silicon Nitride. Scan over 3 wafers, wafers made with different process conditions

Highlights of Helios INLINE-tn

MEASUREMENT OF SILICON NITRIDE

- Layer Thickness: d
- Refractive Index: n (spectral)

WORKS FOR PRODUCTION AND R&D

- inline / each individual wafer
- contactless and non-destructive
- static and dynamic measurement

WORKS FOR ALL RELEVANT WAFER TYPES

- mc-wafers (polished, rough or textured)
- pc-wafers (polished, rough or textured)

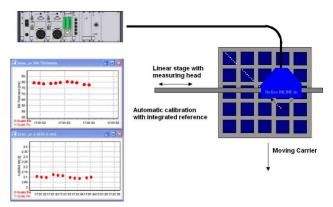
WORKS FOR ALL RELEVANT KIND OF TEXTURES

- isotropic chemically etched
- anisotropic chemically etched
- RIE (Reactive Ion Etched)

WORKS FOR ALL RELEVANT DEPOSITION PROCESSES

- PF-CVD
- Magnetron Sputtering

Installation Example



Diagonal scanning over a 5x5 carrier with solar cells

Inline Operation

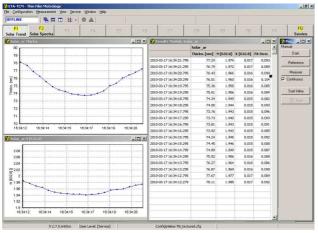
The system is preferably mounted inline, directly after the coating. The scanning can be configured for measuring every individual wafer (few points on every wafer), or for measuring just 1 diagonal line over the carrier (many points on a few wafers on a diagonal line).

The system can also be mounted at a single belt, after individualizing the wafers to a single stream on a transportation belt (multi channel system on request).

Process Steps in which Helios INLINE-tn is used



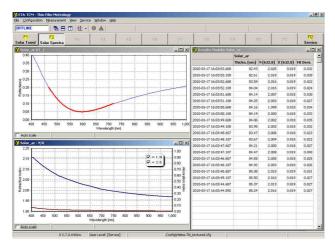
Presentation Examples



Textured mono wafer with SiN-coating. 20 point diagonal scan. Trend display of thickness and refractive index.

Results Module: Solar_ar				
	Solar_ar			
	Thickn. [nm]	N [632.8]	K [632.8]	Fit Devi.
2010-03-17 16:34:21.795	77.24	1.974	0.017	0.093
2010-03-17 16:34:21.295	76.79	1.972	0.017	0.089
2010-03-17 16:34:20.795	76.43	1.966	0.016	0.099
2010-03-17 16:34:20.295	76.01	1.960	0.016	0.104
2010-03-17 16:34:19.795	75.36	1.958	0.016	0.085
2010-03-17 16:34:19.295	75.01	1.956	0.016	0.084
2010-03-17 16:34:18.795	74.34	1.949	0.015	0.082
2010-03-17 16:34:18.295	74.00	1.944	0.015	0.093
2010-03-17 16:34:17.795	73.76	1.943	0.015	0.096
2010-03-17 16:34:17.295	73.73	1.940	0.015	0.093
2010-03-17 16:34:16.795	73.81	1.943	0.015	0.091
2010-03-17 16:34:16.295	73.92	1.943	0.015	0.085
2010-03-17 16:34:15.795	74.24	1.945	0.015	0.092
2010-03-17 16:34:15.295	74.45	1.946	0.015	0.088
2010-03-17 16:34:14.795	74.89	1.949	0.015	0.087
2010-03-17 16:34:14.295	75.52	1.956	0.016	0.088
2010-03-17 16:34:13.795	76.27	1.964	0.016	0.086
2010-03-17 16:34:13.295	76.87	1.969	0.016	0.090
2010-03-17 16:34:12.795	77.67	1.977	0.017	0.089
2010-03-17 16:34:12.279	78.11	1.985	0.017	0.092

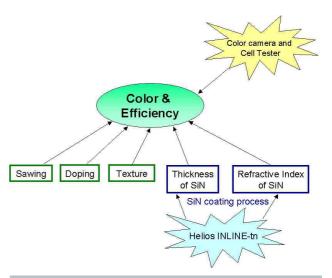
Thickness and refractive index data on the textured mono wafer.



Textured poly wafer with SiN-coating. 20 point diagonal scan. Spectral Reflectance curve, spectral refractive index curve and measured data

Optimize your process parameters

Cell tester/sorter and color cameras are needed for final quality check of the cells, but do not provide direct information, which process parameter is out of the desired process window. Optimizing a production process means, to measure and optimize each single process parameter. This gives full process control and optimized results. The Helios INLINE-tn is designed to give full process control for 2 key process parameters: Thickness and Refractive Index of the AR-coating.



Benefits and ROI of the Helios INLINE-tn

Reduce down-time of your production line

After stopping the line and then re-starting it, the time for getting the production stable into the process window again can be minimized.

This saves material, time andmoney

Save material by sorting out bad wafers early in the production process

Solar wafers with bad quality of the AR-coating can be sorted out directly after the coating. This saves money, since expensive further process steps can be avoided.

This saves material

andmoney

Save labor time for offline testing

The inline process control makes an additional offline testing of thickness and refractive index obsolete.

This saves equipment, labor time

and money

Improve quality and increase efficiency

Reach a more narrow process window of refractive index and layer thickness. This leads to less variation of the color of the cells and to higher efficiency of the solar cell

..... higher value of your solar cells

Calculation Example

A production line produces

- 25 MW of solar cells per year
- cells with average efficiency of 17%
- cells with an average selling price of 1 EURO/cell

Assumed, that the inline measuring system leads to an increase of the average efficiency from 17% -> 17,1%. then this gives a ROI of 150 T€/year

..... earn more money on your cells

Product Specifications

Measurement

Measurement Parameters	Layer Thickness / Refractive Index of SiN (SiO2 and dual layer on request)
Thickness Range	45nm ~ 120nm
Refractive Index Range	1,9 ~ 2,35
Thickness Accuracy	± lnm
Refractive Index Accuracy	± 0,02
Thickness Resolution	< 0,1nm
Refractive Index Resolution	< 0,004
Measurement Speed	< 0,2 s/point (dynamically, on the flight)

Measuring Geometry

Optical Setup	synchronized; 2-channel Reflectance spectrometry; oblique incidence of light; automatic, integrated reference
Measurement Spot Size	~ 5mm x 8mm (elliptically)
Measuring Distance	10 mm (free distance)
Distance Tolerance	± 2mm
Tilt Tolerance	± 2°

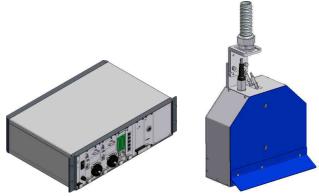
Hardware

Spectrometers	2x diode line spectrometer, 380nm - 1050nm, 16 Bit
Light Source	Halogen, 20 Watts
Line Interfaces	TCP/IP, Digital I/O
Power	AC 100~240V; 50/60Hz
Environment	Temperature: 10-50°C, Humidity: <90% (non-condens.)
Motorized Linear Unit	not included; on request

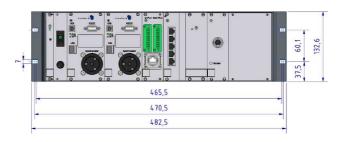
PC / Software

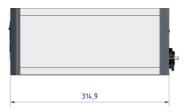
PC Requirements	Windows® 7 / 8 / 10, 8 GB RAM, >500 GB HDD
Software Functions	Reflectance Spectra, Thickness Measurement, Refractive Index Measurement, Trend Displays, Customizable Screensets, Data Storage and Transfer, Various Trigger Functions,

System Dimensions (in mm)



Equipment Overview: Rack with spectrometers (left) and inline measuring head (right)





 ${\it Rack\ with\ Spectrometers,\ power\ supplies,\ LAN-Hub,\ Interfaces;}$

